

# TN0702

# N-Channel Enhancement-Mode Vertical DMOS FET

### Features

- 1.6V Maximum Low Threshold
- · High Input Impedance
- 130 pF Typical Low Input Capacitance
- · Fast Switching Speeds
- Low On-Resistance Guaranteed at  $V_{GS}$  = 2V, 3V and 5V
- Free from Secondary Breakdown
- Low Input and Output Leakage

### Applications

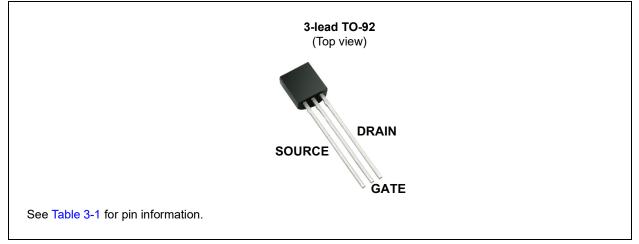
- · Logic-Level Interfaces (Ideal for TTL and CMOS)
- Solid-State Relays
- · Battery-Operated Systems
- Photovoltaic Drives
- · Analog Switches
- · General Purpose Line Drivers
- Telecommunication Switches

### **General Description**

The TN0702 low-threshold Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

### Package Type



# 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings†

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	
Gate-to-Source Voltage	
Operating Ambient Temperature, T <sub>A</sub>	
Storage Temperature, T <sub>S</sub>	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A = 25^{\circ}C$  unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 µs pulse, 2% duty cycle)

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions							
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1 mA							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	0.8	1	V	$V_{GS} = V_{DS}$ , $I_D = 1 \text{ mA}$							
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$			-4	mV/°C	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1 mA ( <b>Note 1</b> )							
Gate Body Leakage Current	I <sub>GSS</sub>	_		100	nA	$V_{GS}$ = ± 20V, $V_{DS}$ = 0V							
	I <sub>DSS</sub>			100	nA	V <sub>GS</sub> = 0V, V <sub>DS</sub> = Maximum rating							
Zero-Gate Voltage Drain Current				100	μA	$V_{DS} = 0.8$ Maximum rating, $V_{GS} = 0V$ , $T_A = 125$ °C (Note 1)							
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1	_	А	$V_{GS} = V_{DS} = 5V$							
			4	5	Ω	V <sub>GS</sub> = 2V, I <sub>D</sub> = 50 mA							
Static Drain-to-Source On-State Resistance	R <sub>DS(ON)</sub>		1.9	2.5	Ω	V <sub>GS</sub> = 3V, I <sub>D</sub> = 200 mA							
	, , , , , , , , , , , , , , , , , , ,	_	1	1.3	Ω	V <sub>GS</sub> = 5V, I <sub>D</sub> = 500 mA							
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$			0.75	%/°C	V <sub>GS</sub> = 5V, I <sub>D</sub> = 500 mA (Note 1)							

Note 1: Specification is obtained by characterization and is not 100% tested.

# AC ELECTRICAL CHARACTERISTICS

<b>Electrical Specifications:</b> $T_A = 25^{\circ}C$ unless otherwise specified. All AC parameters are sample tested.									
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions			
Forward Transconductance	G <sub>FS</sub>	100	500	—	mmho	V <sub>DS</sub> = 5V, I <sub>D</sub> = 500 mA			
Input Capacitance	C <sub>ISS</sub>	—	130	200	pF	$V_{GS} = 0V$			
Common-Source Output Capacitance	C <sub>OSS</sub>	—	70	125	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V,			
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	30	60	pF	f = 1 MHz			
Turn-On Delay Time	t <sub>d(ON)</sub>	_	_	20	ns				
Rise Time		—	—	20	ns	$V_{DD} = 20V,$			
Turn-Off Delay Time	t <sub>d(OFF)</sub>	—	_	30	ns	I <sub>D</sub> = 0.5A, R <sub>GEN</sub> = 25Ω			
Fall Time	t <sub>f</sub>	—	_	20	ns	GEN			
DIODE PARAMETER	DIODE PARAMETER								
Diode Forward Voltage Drop	V <sub>SD</sub>	—	—	1	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 0.5A ( <b>Note 1</b> )			

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle)

## **TEMPERATURE SPECIFICATIONS**

Sym.	Min.	Тур.	Max.	Unit	Conditions			
TEMPERATURE RANGE								
T <sub>A</sub>	-55	_	+150	°C				
Τ <sub>S</sub>	-55	—	+150	°C				
$\theta_{JA}$	—	132		°C/W				
	T <sub>A</sub> T <sub>S</sub>	T <sub>A</sub> -55 T <sub>S</sub> -55	T <sub>A</sub> -55 — T <sub>S</sub> -55 —	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			

### THERMAL CHARACTERISTICS

Package	I <sub>D</sub> (Note 1) (Continuous) (mA)	I <sub>D</sub> (Pulsed) (A)	Power Dissipation at T <sub>A</sub> = 25°C (W)	I <sub>DR</sub> (Note 1) (mA)	I <sub>DRM</sub> (A)
3-lead TO-92	530	1	1	530	1

Note 1:  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

# 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

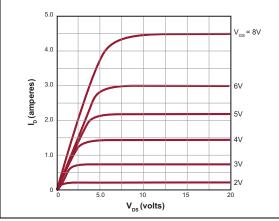


FIGURE 2-1: Output Characteristics.

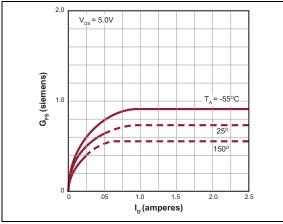


FIGURE 2-2: Transconductance vs. Drain Current.

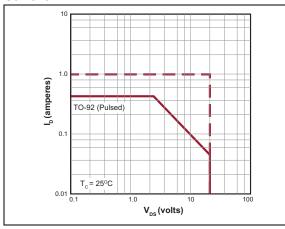
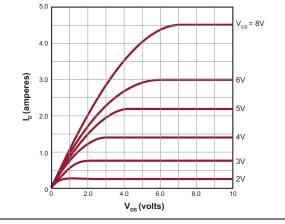


FIGURE 2-3: Maximum Rated Safe Operating Area.





Saturation Characteristics.

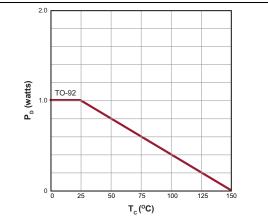


FIGURE 2-5:Power Dissipation vs. CaseTemperature.

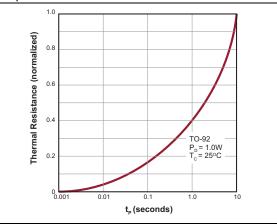
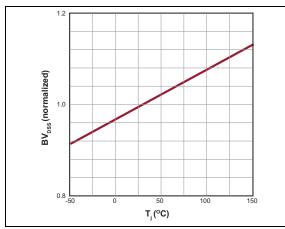


FIGURE 2-6: Characteristics.

Thermal Response





BV<sub>DSS</sub> Variation with

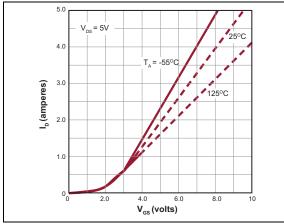


FIGURE 2-8:

Transfer Characteristics.

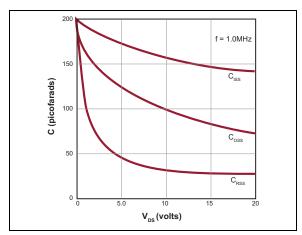
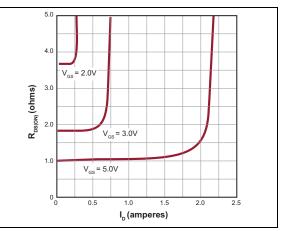


FIGURE 2-9: Capacitance vs. Drain-to-Source Voltage.





On-Resistance vs. Drain

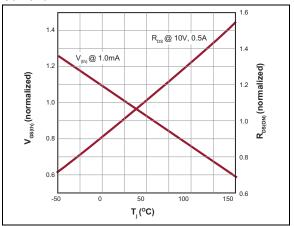


FIGURE 2-11:  $V_{GS(th)}$  and  $R_{DS}$  Variation with Temperature.

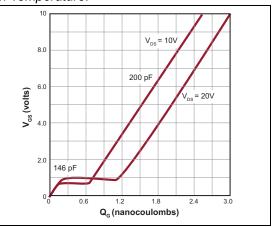


FIGURE 2-12: Characteristics.

Gate Drive Dynamic

## 3.0 PIN DESCRIPTION

Table 3-1 shows the description of pins in TN0702.Refer to Package Type for the location of pins.

### TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Source	Source
2	Gate	Gate
3	Drain	Drain

## 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for TN0702.

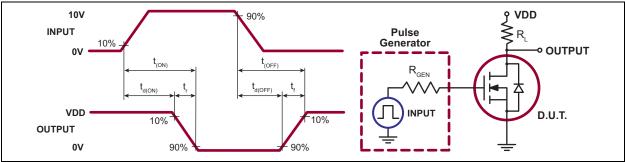


FIGURE 4-1: Switching Waveforms and Test Circuit.

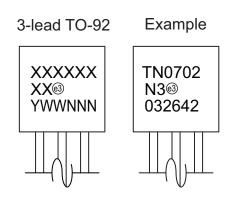
### TABLE 4-1: PRODUCT SUMMARY

BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub> (Maximum) (Ω)	I <sub>D(ON)</sub> (Minimum) (A)	V <sub>GS(th)</sub> (Maximum) (V)
20	1.3	0.5	1

# TN0702

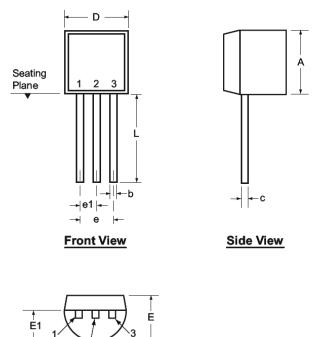
## 5.0 PACKAGING INFORMATION

## 5.1 Package Marking Information



Legend	: XXX Y YY WW NNN @3 *	Product Code or Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC <sup>®</sup> designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
Note:	be carrie characters	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for product code or customer-specific information. Package may or e the corporate logo.

# 3-Lead TO-92 Package Outline (L/LL/N3)



**Bottom View** 

Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symb	ol	А	b	с	D	E	E1	е	e1	L
	MIN	.170	.014 <sup>†</sup>	.014†	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
(	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92. \* This dimension is not specified in the JEDEC drawing. † This dimension differs from the JEDEC drawing. Drawings not to scale.

# TN0702

NOTES:

# APPENDIX A: REVISION HISTORY

### **Revision A (September 2020)**

- Converted Supertex Doc# DSFP-TN0702 to Microchip DS20005941A
- · Changed the package marking format
- Removed the TO-92 N3 P002, P003, P005, P013, and P014 media types to align package specifications with the actual BQM
- Made minor text changes throughout the document

# **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	<u> </u>		- <u>x</u> - <u>x</u>	Example:	
Device	Packa Optio		Environmental Media Type	a) TN0702N3-G:	N-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92,1000/Bag
Device:	TN0702	=	N-Channel Enhancement-Mode Vertical DMOS FET		
Package:	N3	=	3-lead TO-92		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	1000/Bag for an N3 Package		

### Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods being used in attempts to breach the code protection features of the Microchip devices. We believe that these methods require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Attempts to breach these code protection features, most likely, cannot be accomplished without violating Microchip's intellectual property rights.
- Microchip is willing to work with any customer who is concerned about the integrity of its code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not
  mean that we are guaranteeing the product is "unbreakable." Code protection is constantly evolving. We at Microchip are
  committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection
  feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or
  other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication is provided for the sole purpose of designing with and using Microchip products. Information regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications.

THIS INFORMATION IS PROVIDED BY MICROCHIP "AS IS". MICROCHIP MAKES NO REPRESENTATIONS OR WAR-RANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION INCLUDING BUT NOT LIMITED TO ANY IMPLIED WARRANTIES OF NON-INFRINGEMENT, MERCHANTABILITY, AND FITNESS FOR A PARTICULAR PURPOSE OR WARRANTIES RELATED TO ITS CONDITION, QUALITY, OR PERFOR-MANCE.

IN NO EVENT WILL MICROCHIP BE LIABLE FOR ANY INDI-RECT, SPECIAL, PUNITIVE, INCIDENTAL OR CONSEQUEN-TIAL LOSS, DAMAGE, COST OR EXPENSE OF ANY KIND WHATSOEVER RELATED TO THE INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROCHIP HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROCHIP'S TOTAL LIABILITY ON ALL CLAIMS IN ANY WAY RELATED TO THE INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, THAT YOU HAVE PAID DIRECTLY TO MICROCHIP FOR THE INFORMATION. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated

#### For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

#### Trademarks

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, chipKIT, chipKIT logo, CryptoMemory, CryptoRF, dsPIC, FlashFlex, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PackeTime, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TempTrackr, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, FlashTec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, Vite, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, Anyln, AnyOut, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, EtherGREEN, In-Circuit Serial Programming, ICSP, INICnet, Inter-Chip Connectivity, JitterBlocker, KleerNet, KleerNet Iogo, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified Iogo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, SAM-ICE, Serial Quad I/O, SMART-I.S., SQI, SuperSwitcher, SuperSwitcher II, Total Endurance, TSHARC, USBCheck, VariSense, ViewSpan, WiperLock, Wireless DNA, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, and Symmcom are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2020, Microchip Technology Incorporated, All Rights Reserved.

ISBN: 978-1-5224-6791-5



# Worldwide Sales and Service

### AMERICAS

**Corporate Office** 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: http://www.microchip.com/ support

Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Austin, TX Tel: 512-257-3370

**Boston** Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

Dallas Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Novi, MI Tel: 248-848-4000

Houston, TX Tel: 281-894-5983

Indianapolis Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453 Tel: 317-536-2380

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608 Tel: 951-273-7800

Raleigh, NC Tel: 919-844-7510

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110 Tel: 408-436-4270

Canada - Toronto Tel: 905-695-1980 Fax: 905-695-2078

### ASIA/PACIFIC

Australia - Sydney Tel: 61-2-9868-6733

China - Beijing Tel: 86-10-8569-7000 China - Chengdu

Tel: 86-28-8665-5511 China - Chongqing Tel: 86-23-8980-9588

China - Dongguan Tel: 86-769-8702-9880

China - Guangzhou Tel: 86-20-8755-8029

China - Hangzhou Tel: 86-571-8792-8115

China - Hong Kong SAR Tel: 852-2943-5100

China - Nanjing Tel: 86-25-8473-2460

China - Qingdao Tel: 86-532-8502-7355

China - Shanghai Tel: 86-21-3326-8000

China - Shenyang Tel: 86-24-2334-2829

China - Shenzhen Tel: 86-755-8864-2200

China - Suzhou Tel: 86-186-6233-1526

China - Wuhan Tel: 86-27-5980-5300

China - Xian Tel: 86-29-8833-7252

China - Xiamen Tel: 86-592-2388138

China - Zhuhai Tel: 86-756-3210040

### ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444

India - New Delhi Tel: 91-11-4160-8631

Tel: 91-20-4121-0141

Tel: 81-6-6152-7160

Tel: 81-3-6880- 3770

Tel: 82-53-744-4301

Tel: 82-2-554-7200

Tel: 63-2-634-9065

Taiwan - Kaohsiung

Tel: 886-2-2508-8600

Thailand - Bangkok

Vietnam - Ho Chi Minh Tel: 84-28-5448-2100

Tel: 31-416-690399 Fax: 31-416-690340

EUROPE

Austria - Wels

Tel: 43-7242-2244-39

Tel: 45-4485-5910

Fax: 45-4485-2829

Tel: 358-9-4520-820

Tel: 33-1-69-53-63-20

Fax: 33-1-69-30-90-79

**Germany - Garching** 

Tel: 49-2129-3766400

Germany - Heilbronn

Germany - Karlsruhe

Tel: 49-7131-72400

Tel: 49-721-625370

Germany - Munich

Tel: 49-89-627-144-0

Fax: 49-89-627-144-44

Germany - Rosenheim

Tel: 49-8031-354-560

Israel - Ra'anana

Italy - Milan

Italy - Padova

Tel: 972-9-744-7705

Tel: 39-0331-742611

Fax: 39-0331-466781

Tel: 39-049-7625286

**Netherlands - Drunen** 

Tel: 49-8931-9700

Germany - Haan

Finland - Espoo

France - Paris

Fax: 43-7242-2244-393

**Denmark - Copenhagen** 

Norway - Trondheim Tel: 47-7288-4388

Poland - Warsaw Tel: 48-22-3325737

**Romania - Bucharest** Tel: 40-21-407-87-50

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

Sweden - Gothenberg Tel: 46-31-704-60-40

Sweden - Stockholm Tel: 46-8-5090-4654

**UK - Wokingham** Tel: 44-118-921-5800 Fax: 44-118-921-5820

India - Pune Japan - Osaka

Japan - Tokyo

Korea - Daegu

Korea - Seoul

Malaysia - Kuala Lumpur Tel: 60-3-7651-7906

Malaysia - Penang Tel: 60-4-227-8870

Singapore

Taiwan - Hsin Chu Tel: 886-3-577-8366

Tel: 886-7-213-7830

Taiwan - Taipei

Tel: 66-2-694-1351

Philippines - Manila

Tel: 65-6334-8870